

DIODE

D222-32, D222-32X

<ul style="list-style-type: none"> ◆ $V_{RRM} = \underline{100 - 1600 V}$ ◆ $I_{F(AV)} = \underline{32 A}$ ($T_C = 150\text{ °C}$) ◆ $I_{FSM} = \underline{0,46 kA}$ ($T_j = 190\text{ °C}$) 		
<ul style="list-style-type: none"> ◆ Hermetic metal cases with glass insulators ◆ Threaded studs of ISO 		

MAXIMUM RATED VALUES

Parameter and conditions	Symbol	Values	Units
Repetitive peak reverse voltage, $T_j = -60 \dots + 190\text{ °C}$	V_{RRM}	100-1600	V
Non- repetitive peak reverse voltage, $T_j = -60 \dots + 190\text{ °C}$	V_{RSM}	200-1700	
Repetitive peak reverse current, $T_j = 190\text{ °C}$, $V_R = V_{RRM}$	I_{RRM}	5	mA
Maximum average forward current, $f = 50\text{ Hz}$, $T_C = 150\text{ °C}$	$I_{F(AV)}$	32	A
RMS forward current, $f = 50\text{ Hz}$, $T_C = 140\text{ °C}$	I_{FRMS}	50	
Surge non-repetitive current, $T_j = 190\text{ °C}$, $V_R = 0$, $t_p = 10\text{ ms}$	I_{FSM}	0,46	kA
Safety factor	I^2t	1,06	kA ² s
Operation junction temperature range	T_j	-60 to +190	°C
Storage temperature range	T_{stg}	-60 to +50	°C

ELECTRICAL CHARACTERISTICS

Parameter and conditions	Symbol	Values			Units
		min	typ.	max	
Maximum peak forward voltage, $T_j = 25\text{ °C}$, $I_F = 100\text{ A}$	V_{FM}	-	-	1,35	V
On-state threshold voltage, $T_j = 190\text{ °C}$, $I_F = 50 - 150\text{ A}$	V_{TO}	-	-	0,856	
On-state slope resistance, $T_j = 190\text{ °C}$, $I_F = 50 - 150\text{ A}$	r_T	-	-	6,5	mΩ

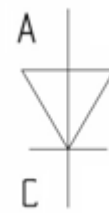
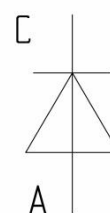
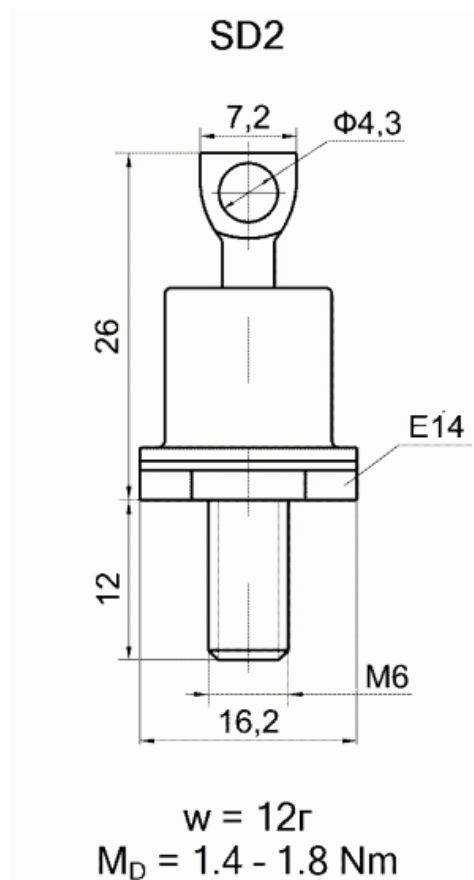


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THERMAL PARAMETERS					
Thermal resistance junction to case	$R_{th(j-c)}$	-	-	0,9	°C/W
Thermal resistance case to heatsink	$R_{th(c-h)}$	-	-	0,7	
MECHANICAL PARAMETERS					
Weight	w	-	0,012	-	kg
Mounting torque	M_d	1,4	-	1,8	Nm



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C – Cathode, A – Anode

Device Outline Drawing

(dimensions in mm)



126, Proletarskaya str.,

430001, Saransk, Republic Mordovia, Russia

Tel: +7(8342) 47-04-30

Tel/Fax: +7 (8342) 47-15-01

E-mail: vpruvs@elvpr.ru

Internet: www.elvpr.ru Internet: www.elvpr.ru